

Silicon Epitaxial Planar Switching Diode

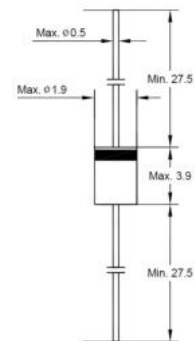


FEATURES:

High voltage switching diode

DO-35 glass case

High reliability



Glass Case DO-35
Dimensions in mm

SPECIFICATION:

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Reverse Voltage	V_R	200	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1	A
at $t = 1$ s		3	
at $t = 100 \mu\text{s}$		9	
Total Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	250	-	V
Forward Voltage at $I_F = 100$ mA at $I_F = 200$ mA	V_F	- -	1 1.25	V
Reverse Current at $V_R = 200$ V	I_R	-	100	nA
at $V_R = 200$ V, $T_A = 150^\circ\text{C}$		-	100	μA
Diode Capacitance at $V_R = 0$ V, $f = 1$ MHz	C_d	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30$ mA, $I_{tr} = 3$ mA, $R_L = 100 \Omega$	t_{rr}	-	50	ns

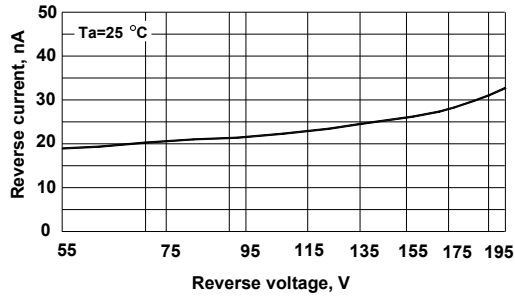
Art. Nr.

RND BAV21

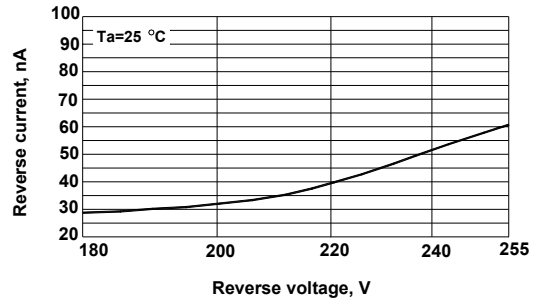
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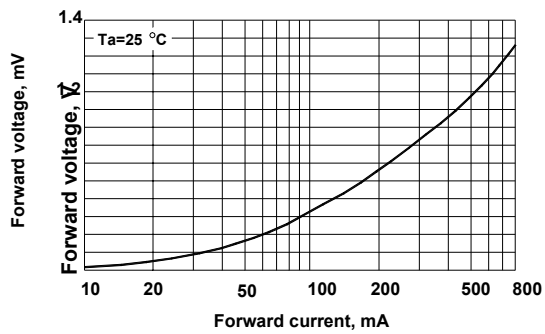
Reverse current vs. reverse voltage



Reverse current vs. reverse voltage



Forward voltage vs. forward current



Capacitance vs. reverse voltage

